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PATENT NUMBER

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A	PPLICATION NO. 09/995575	CONT/PRIOR	<b>CLASS</b> 438	SUBCLASS	ART UNIT	EXAMINER .				
APPLICANTS	Tamihide Yasumoto  Bemiconductor device manufacturing method using metal silicide reaction after ion implantation  July 2009  PTO-2012099									
TITLE	in Silicon (	#1: IV:					PTO-2040 12/99			

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ISSUING CLASSIFICATION										
ORIGIN	CROSS REFERENCE(S)									
CLASS	SUBCLASS	CLASS	SUBCLASS (ONE SUBCLASS PER BLOCK)							
INTERNATIONA	L CLASSIFICATION									
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TERMINAL	DRAWINGS			CLAIMS ALLOWED		
TERMINAL DISCLAIMER	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.	
MARKET STATE OF THE STATE OF TH				NOTICE OF ALLOWANCE MAILED		
The term of this patent. (date)	*					
has been disclaimed.	(Assistant Examiner)		(Date)			
The term of this patent shall not extend beyond the expiration date	*					
of U.S Patent: No.				ISSUE FEE		
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this patent have been disclaimed.	(Legal Instrum	nents Examiner)	(Date)			
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